NST489AMT1G, NSVT489AMT1G

High Current Surface Mount NPN Silicon Low V_{CE(sat)} Switching Transistor for Load Management in Portable Applications

Features

- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS $(T_A = 25^{\circ}C)$

| Rating | Symbol | Max | Unit |
|--------------------------------|------------------|-----|------|
| Collector-Emitter Voltage | V _{CEO} | 30 | V |
| Collector-Base Voltage | V _{CBO} | 50 | V |
| Emitter-Base Voltage | V _{EBO} | 5.0 | V |
| Collector Current – Continuous | I _C | 2.0 | Α |
| Collector Current – Peak | I _{CM} | 3.0 | Α |

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|--|--|--------------|-------------|
| Total Device Dissipation T _A = 25°C Derate above 25°C | P _D (Note 1) | 535 4.3 | mW mW/°C |
| Thermal Resistance, Junction-to-Ambient | R _{θJA} (Note 1) | 234 | °C/W |
| Total Device Dissipation T _A = 25°C Derate above 25°C | P _D (Note 2) | 1.180 9.4 | W mW/°C |
| Thermal Resistance, Junction-to-Ambient | R _{θJA} (Note 2) | 106 | °C/W |
| Thermal Resistance, Junction-to-Lead #1 | R _{0JL} (Note 1) R _{0JL} (Note 2) | 110 50 | °C/W |
| Total Device Dissipation (Single Pulse < 10 s) | P _{Dsingle} (Notes 2 and 3) | 1.75 | W |
| Junction and Storage Temperature Range | T _J , T _{stg} | -55 to +150 | °C |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. FR-4 with 1 oz and 3.9 mm² of copper area.
- 2. FR-4 with 1 oz and 645 mm² of copper area.
- 3. Refer to Figure 8.



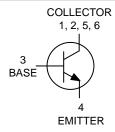
ON Semiconductor®

www.onsemi.com

30 VOLTS, 3.0 AMPS NPN TRANSISTOR



TSOP-6 CASE 318G STYLE 6



DEVICE MARKING



N2 = Specific Device Code

M = Date Code*

= Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

| Device | Package | Shipping [†] |
|--------------|---------------------|------------------------|
| NST489AMT1G | TSOP-6 (Pb-Free) | 3,000 / Tape & Reel |
| NSVT489AMT1G | TSOP-6 (Pb-Free) | 3,000 / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

| Characteristic | | Symbol | Min | Тур | Max | Unit |
|--|--|----------------------|-------------------|----------------------|-------------------------|------|
| OFF CHARACTERISTICS | | | | | | |
| Collector – Emitter Breakdown Voltage (I _C = 10 mA | $I_{A}, I_{B} = 0$ | V _{(BR)CEO} | 30 | _ | _ | V |
| Collector-Base Breakdown Voltage (I _C = 0.1 mA, | I _E = 0) | V _{(BR)CBO} | 50 | - | - | V |
| Emitter-Base Breakdown Voltage (I _E = 0.1 mA, I _C = 0) | | V _{(BR)EBO} | 5.0 | - | - | V |
| Collector Cutoff Current (V _{CB} = 30 V, I _E = 0) | | I _{CBO} | _ | - | 0.1 | μΑ |
| Collector–Emitter Cutoff Current (V _{CES} = 30 V) | | I _{CES} | _ | - | 0.1 | μΑ |
| Emitter Cutoff Current (V _{EB} = 4.0 V) | | I _{EBO} | _ | _ | 0.1 | μΑ |
| ON CHARACTERISTICS | ON CHARACTERISTICS | | | | | |
| DC Current Gain (Note 4) | | h _{FE} | 300 300 200 | 500 - | 900 - | |
| Collector - Emitter Saturation Voltage (Note 4) | $(I_C = 1.0 \text{ A}, I_B = 100 \text{ mA})$ $(I_C = 0.5 \text{ A}, I_B = 50 \text{ mA})$ $(I_C = 0.1 \text{ A}, I_B = 1.0 \text{ mA})$ | V _{CE(sat)} | - - - | 0.10 0.06 0.05 | 0.200 0.125 0.075 | V |
| Base – Emitter Saturation Voltage (Note 4) (I _C = 1.0 A, I _B = 0.1 A) | | V _{BE(sat)} | _ | - | 1.1 | V |
| Base – Emitter Turn–on Voltage (Note 4) (I _C = 1.0 A, V _{CE} = 2.0 V) | | V _{BE(on)} | _ | _ | 1.1 | V |
| Cutoff Frequency ($I_C = 100 \text{ mA}$, $V_{CE} = 5.0 \text{ V}$, $f = 100 \text{ MHz}$ | | f⊤ | 200 | 300 | - | MHz |
| Output Capacitance (f = 1.0 MHz) | | C _{obo} | _ | _ | 15 | pF |

^{4.} Pulsed Condition: Pulse Width \leq 300 μ sec, Duty Cycle \leq 2%.

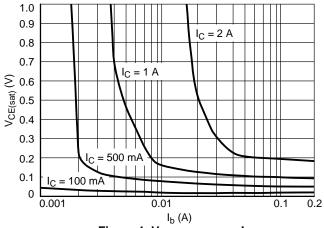
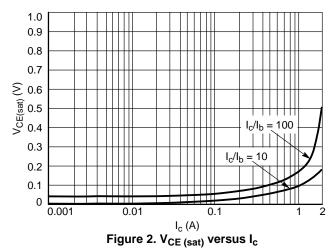


Figure 1. $V_{CE (sat)}$ versus I_b



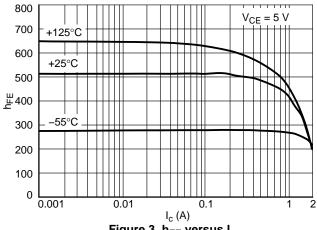


Figure 3. h_{FE} versus I_c

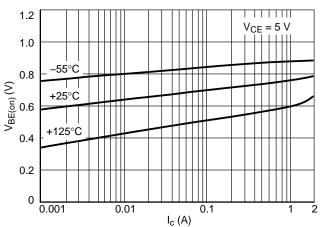
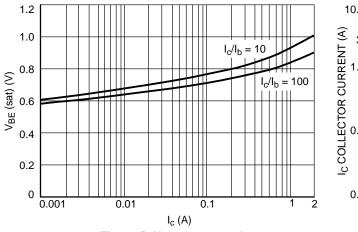


Figure 4. $V_{\rm BE(on)}$ versus $I_{\rm c}$

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10.00

3.0

1.00

0.10

SINGLE PULSE T_{amb} = 25°C

0.01

0.10

1.00

VCE(sat) (V)

100.00

Figure 5. $V_{BE(sat)}$ versus I_c

Figure 6. Safe Operating Area

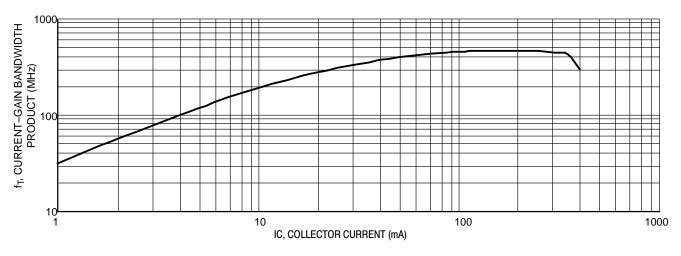


Figure 7. f_T (MHZ) versus I_C (mA) V_{CE} = 5.0 V

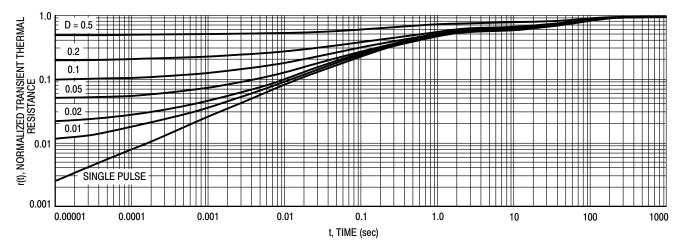


Figure 8. Normalized Thermal Response



TSOP-6 CASE 318G-02 **ISSUE V**

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DATE 12 JUN 2012

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM
- LEAD THIORNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSIONS D
- AND E1 ARE DETERMINED AT DATUM H.
 PIN ONE INDICATOR MUST BE LOCATED IN THE INDICATED ZONE.

| | MILLIMETERS | | | |
|-----|-------------|------|------|--|
| DIM | MIN | NOM | MAX | |
| Α | 0.90 | 1.00 | 1.10 | |
| A1 | 0.01 | 0.06 | 0.10 | |
| b | 0.25 | 0.38 | 0.50 | |
| С | 0.10 | 0.18 | 0.26 | |
| D | 2.90 | 3.00 | 3.10 | |
| E | 2.50 | 2.75 | 3.00 | |
| E1 | 1.30 | 1.50 | 1.70 | |
| е | 0.85 | 0.95 | 1.05 | |
| L | 0.20 | 0.40 | 0.60 | |
| L2 | 0.25 BSC | | | |
| N.A | 00 | | 4.00 | |

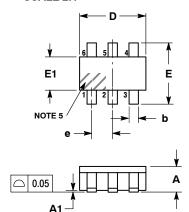
STYLE 5:

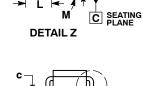
PIN 1. EMITTER 2

2. BASE 2 3. COLLECTOR 1 4. EMITTER 1

BASE 1

6. COLLECTOR 2





Н

| c T | |
|----------|--|
| DETAIL Z | |

| STYLE 1: PIN 1. DRAIN 2. DRAIN 3. GATE 4. SOURCE 5. DRAIN 6. DRAIN | STYLE PIN |
|--|--------------|
| STYLE 7: PIN 1. COLLECTOR 2. COLLECTOR 3. BASE 4. N/C | STYLI PIN |

COLLECTOR

6. EMITTER

2. SOURCE 2

3. GATE 2

4. DRAIN 2

5. SOURCE 1

DRAIN 1

STYLE 13: PIN 1. GATE 1

1. EMITTER 2 2. BASE 1 3. 4. COLLECTOR 1 EMITTER 1 BASE 2 6. COLLECTOR 2

E 8: Vbus 2. D(in) 3. D(in)+ 4. D(out)+ 5. D(out) 6. GND

STYLE 14: PIN 1. ANODE SOURCE 3 GATE CATHODE/DRAIN CATHODE/DRAIN 5. CATHODE/DRAIN

2. N/C 3. R BOOST 4. Vz 5. V in 6. V out STYLE 9: PIN 1. LOW VOLTAGE GATE

STYLE 3:

PIN 1. ENABLE

2. DRAIN

3. SOURO

SOURCE

5. DRAIN 6. HIGH VOLTAGE GATE STYLE 15: PIN 1. ANODE SOURCE

3. GATE DRAIN 5. N/C 6. CATHODE STYLE 4: PIN 1. N/C 2. V in 3. NOT USED 4. GROUND 5. ENABLE 6. LOAD

STYLE 10 PIN 1. D(OUT)+ 2. GND 3. D(OUT)-4. D(IN)-

5. VBUS 6. D(IN)+ STYLE 16: PIN 1. ANODE/CATHODE

2. BASE

5. ANODE

3 FMITTER

COLLECTOR

CATHODE

PIN 1. SOURCE 1 2. DRAIN 2 DRAIN 2 4 SOURCE 2 5. GATE 1 6. DRAIN 1/GATE 2 STYLE 17: PIN 1. EMITTER

2. BASE

STYLE 11:

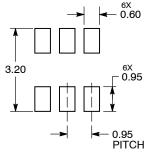
5. COLLECTOR 6. COLLECTOR STYLE 12: 2. GROUND

3. I/O 4. I/O 6. I/O

STYLE 6: PIN 1. COLLECTOR 2. COLLECTOR

3 BASE 4. EMITTER

RECOMMENDED **SOLDERING FOOTPRINT***



DIMENSIONS: MILLIMETERS

GENERIC MARKING DIAGRAM*

3 ANODE/CATHODE

CATHODE

COLLECTOR





XXX = Specific Device Code Α =Assembly Location

Υ = Year

W = Work Week = Pb-Free Package XXX = Specific Device Code M = Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot ' ", may or may not be present.

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